

**TECHNICAL DATA** DATA SHEET 262, REV -

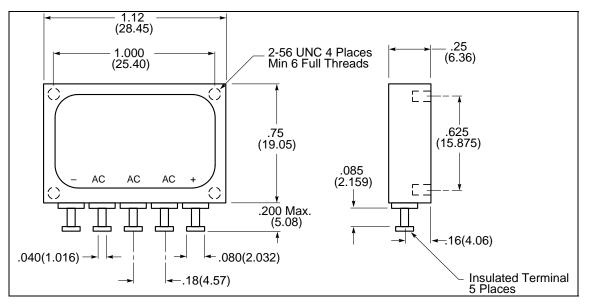
# THREE PHASE FULL WAVE **BRIDGE RECTIFIER ASSEMBLY**

DESCRIPTION: 1000 VOLT, 7.5 AMP, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAX. RATINGS / ELECTRICAL CHARACTERISTICS

All ratings are at  $T_A = 25^{\circ}C$  unless otherwise specified. RATING CONDITIONS MIN ΤΥΡ MAX UNIT Peak Inverse Voltage --Vdc -1000 (PIV) Average DC Output  $T_{\rm C} = 55 \,^{\circ}{\rm C}$ 7.5 Amps Current ( $T_c$  = Case Temp)  $T_{\rm C} = 100 \,{}^{\circ}{\rm C}$ 5.5  $(I_{o})$  $T_{c} = 125 °C$ 3.75  $T_A = 25 \degree C$ Average DC Output 3.0 Amps Current Ambient Temp.  $T_{A} = 55^{\circ}C$ 2.3 (no heat sink)  $(I_o)$  $T_{A} = 100^{\circ}C$ 1.5 Peak Single Cycle Surge  $t_p = 8.3 \text{ ms Single}$ 50 Amps(pk) \_ \_ Half Cycle Sine Current (I<sub>FSM</sub>) Wave, Superimposed On Rated Load Peak Recurring Surge  $T_A = 25 \,^{\circ}C$ \_ 15 Amps \_ Current (I<sub>FRM</sub>) **Operating and Storage** -55 +150 °C -\_ Temp. (T<sub>op</sub> & T<sub>sta</sub>) Maximum Forward  $I_f = 3.0A (300 \ \mu sec$ 1.4 Volts -\_ Voltage (V<sub>f</sub>) pulse, duty cycle < 2%) μAmps Maximum Instantaneous  $T_A = 25^\circ C$ 5.0 \_ \_ **Reverse Current At Rated** 100  $T_{A} = 100^{\circ} C$ (PIV) **Reverse Recovery Time**  $I_f = 0.5A, I_r = 1.0A, I_{rr}$ \_ \_ 5000 nsec = 0.25A (t<sub>rr</sub>) -4.5 °C/W Thermal Resistance  $(\theta_{,\parallel})$ -\_

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# MECHANICAL DIMENSIONS: In Inches / mm

## FIG. 405

Note: Case finish - Black Anodized

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